Dual Nano-power Open Drain Output Comparator

The NCS3402 is a nano-power comparator consuming only 470 nA per channel supply current, which make this device ideal for battery power and wireless handset applications.

The NCS3402 has a minimum operating supply voltage of 2.7 V over the extended industrial temperature range ($T_A = -40^{\circ}C$ to 125°C), while having an input common-mode range of -0.1 to $V_{DD} + 5$ V.

The ultra low supply current makes the NCS3402 an ideal choice for battery powered and portable applications where quiescent current is the primary concern. Reverse battery protection guards the amplifier from an over-current condition due to improper battery installation. For harsh environments, the inputs can be taken 5 V above the positive supply rail without damage to the device.

Features

- Low Supply Current: 470 nA/Per Channel
 - Input Common–Mode Range exceeds the rails
 - -0.1 V to VDD + 5 V
- Supply Voltage Range: 2.7 V to 16 V
- Reverse Battery Protection Up to 18 V
- Open Drain CMOS Output Stage
- Specified Temperature Range
 - −40°C to 125°C
- This is a Pb–Free Device

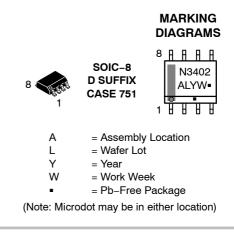
Typical Applications

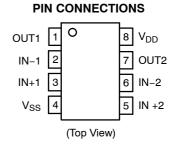
- Voltage Sense Circuit
- PSU Monitoring Circuit
- Wireless Handsets
- Portable Medical Equipment



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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

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PIN FUNCTION DESCRIPTION

Pin No.	Pin Name	Description	
1	OUT1	Channel 1 Output	
2	IN-1	Channel 1 Inverting Input	
3	IN+2	Channel 2 Non-Inverting Input	
4	V _{SS}	Negative Power Supply	
5	IN+2	Channel 2 Non-Inverting Input	
6	IN-2	Channel 2 Inverting Input	
7	OUT2	Channel 2 Output	
8	V _{DD}	Positive Power Supply	

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	V _{DD}	17	V
Differential Input Voltage	V _{ID}	±20	V
Input Voltage Range (Notes 1 and 2)	V _{IN}	0 to V _{CC} + 5	V
Input Current Range	I _{IN}	±10	mA
Output Current Range	lo	±10	mA
Operating Free-Air Temperature Range	T _A	-40 to +125	°C
Maximum Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{STG}	-65 to 150	°C
Lead Temperature 1.6 mm (1/16 inch) from case for 10 seconds	T _{SLD}	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. All voltage values, except differential voltages, are respect to GND 2. Input voltage range is limited to 20V or V_{CC} +5 V whichever is smaller

ESD RATINGS

Rating	Symbol	Value	Unit
Human Body Model	HBM	2000	V
Machine Model	MM	200	V

THERMAL CHARACTERISTICS (Note 3)

Rating	Symbol	Value	Unit
Thermal Characteristics Thermal Resistance, Junction-to-Air SOIC8	R_{\thetaJA}	176	°C/W

3. Power dissipation must be considered to ensure the maximum junction temperature (θ_{JA}) is not exceeded.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol		Min	Max	Unit
Supply voltage	V _{DD}	Single supply	2.7	16	V
		Split supply	±1.35	±8	
Common-mode input voltage range	V _{ICR}		-0.1	V _{DD} +5	V
Operating free-air temperature	T _A		- 40	125	°C

DC PERFORMANCE ELECTRICAL CHARACTERISTICS AT SPECIFIED OPERATING FREE-AIR TEMPERATURE, V_S = 2.7 V, 5 V, 15 V (unless otherwise noted)

Parameter	Symbol	Testing Conditions	TA	Min	Тур	Max	Unit
			25°C		250	3600	
Input offset voltage	V _{IO}	V_{CM} = V_S /2, R_S = 50 Ω , R_P = 1 M Ω	Full range			4400	μV
Offset voltage drift	ΔV_{IO}		25°C		3		μV/°C
			25°C	55	72		
	CMRR	V_{CM} = 0 to 2.7 V, R_S = 50 Ω	Full range	50			
Common mode rejection		V_{CM} = 0 to 5 V, R_{S} = 50 Ω	25°C	60	76		
Common-mode rejection ratio			Full range	55			dB
			25°C	65	88		
		V_{CM} = 0 to 15 V, R_S = 50 Ω	Full range	60			
Large-signal differential voltage amplification	A _{VD}	R _P = 1 MΩ	25°C		1000		V/mV

INPUT/OUTPUT CHARACTERISTICS SPECIFIED OPERATING FREE-AIR TEMPERATURE,

 V_S = 2.7 V, 5 V, 15 V (unless otherwise noted)

Input offset current				20	100	
(Note 4)	Ι _{ΙΟ}	V _{CM} = V _S /2, R _P = 1 MΩ, R _S = 50 Ω	Full range		1000	pА
Input biog ourrept		$v_{CM} = v_{S/2}, n_p = 1 \text{ Miss}, n_S = 50 \text{ ss}$	25°C	80	250	
Input bias current (Note 4)	I _{IB}		Full range		3000	pА
Differential input resistance	R _{ID}	V _{in} = V _S /2	25°C	300		MΩ
High-impedance output leakage current	I _{OZ}	$V_{CM} = V_S/2$, $V_O = V_{CC}$, $V_{ID} = 1 V$	25°C	50		pА
	V _{OL}	$V_{CM} = V_S/2$, $I_{OL} = 2 \ \mu A$, $V_{ID} = -1 \ V$	25°C	8		
Low-level output voltage			25°C	80	200	mV
		$V_{CM} = V_S/2$, $I_{OL} = 50 \ \mu A$, $V_{ID} = -1 \ V$	Full range		300	

POWER SUPPLY SPECIFIED OPERATING FREE-AIR TEMPERATURE, V_{CC} = 2.7 V, 5 V, 15 V (unless otherwise noted)

Supply current (per				25°C		470	550			
			Output state low	Full range			750	- 0		
channel)	ICC	$R_P = No pullup$		25°C		560	640	nA		
		Output state high	Full range			950				
Power supply rejection ratio		V _{CM} = V _S /2, No		25°C	75	100				
	PSRR		V _{CM} = V _S /2, No	V _{CM} = V _S /2, No	V _{CM} = V _S /2, No load	V_{CC} = 2.7 V to 5 V	Full range	70		
	Fonn	load		25°C	85	105		uВ		
			V_{CC} = 5 V to 15 V	Full range	80					

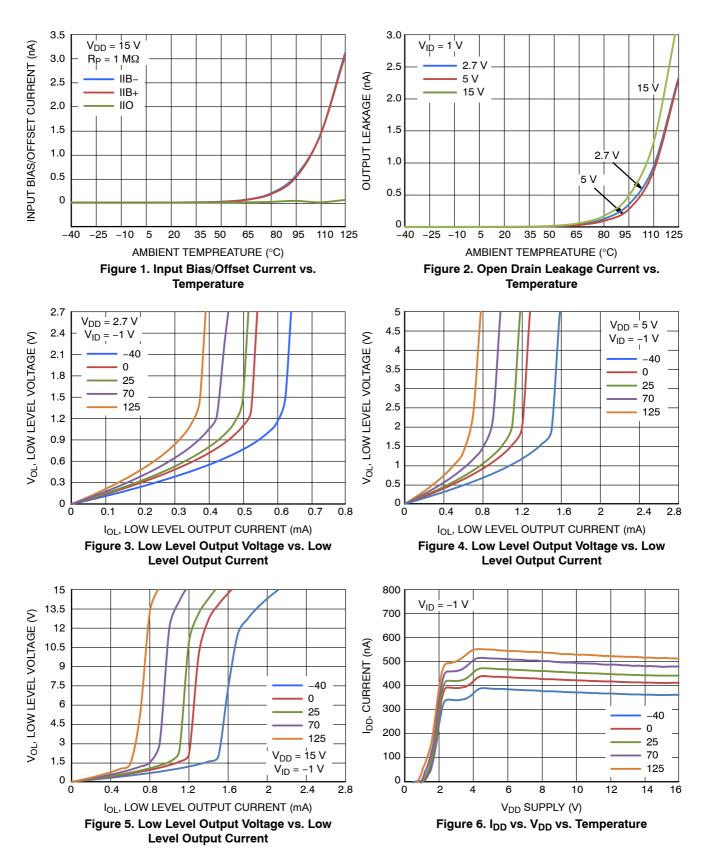
4. Guaranteed by design or characterization.

SWITCHING CHARACTERISTICS AT RECOMMENDED OPERATING CONDITIONS,

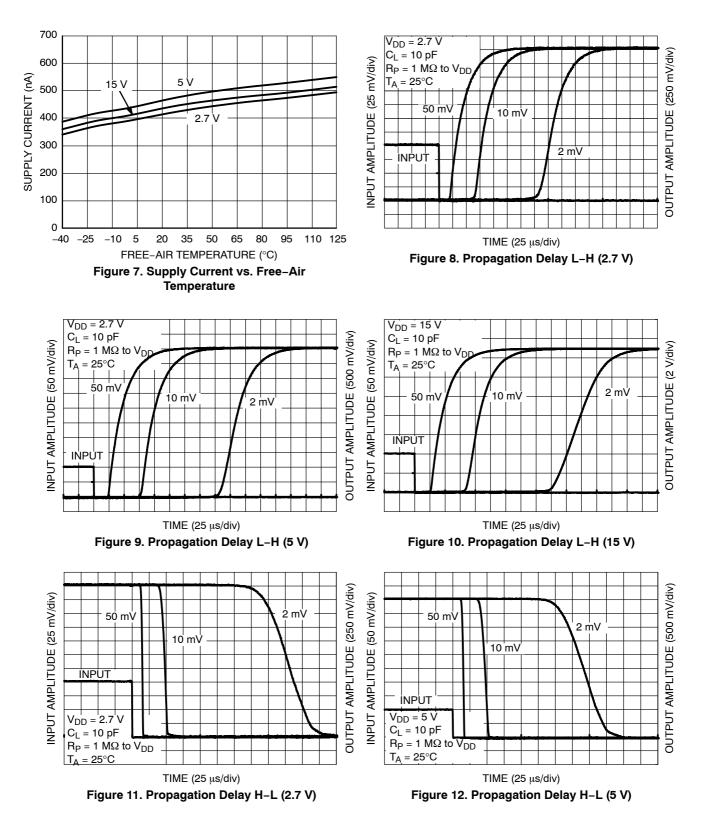
 V_{CC} = 2.7 V, 5 V, 15 V, T_A = 25°C (unless otherwise noted)

Parameter	Symbol	Testing Conditions		T _A	Min	Тур	Max	Unit
			Overdrive = 2 mV			220		
Propagation delay time, low-to-high-level	t _(PLH)	f = 10 kHz, VSTEP = 100 mV, $R_P = 1 M\Omega,$ $C_L = 10 \text{ pF}$	Overdrive = 10 mV	25°C		85		
ion to ingli ioroi			Overdrive = 50 mV			30		
			Overdrive = 2 mV	25°C		250		μs
Propagation delay time, high-to-low-level output			Overdrive = 10 mV			55		
5			Overdrive = 50 mV			18		
Fall time	tf	R _P = 1 MΩ, C _L = 10 pF		25°C		5		μs

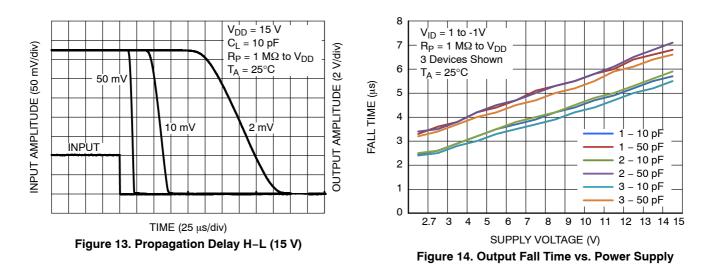
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS



ORDERING INFORMATION

Device	Package	Shipping [†]
NCS3402DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. COLLECTOR, #2 4 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

7.

8. GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. 5. GATE, #2 SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3 ANODE 1 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 2 OVI 0 З. UVLO 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: ANODE PIN 1. ANODE 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. COLLECTOR/ANODE 8. STYLE 28: 11. SW_TO_GND 2. DASIC OFF PIN 1. DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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COLLECTOR, #1

COLLECTOR, #1

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